



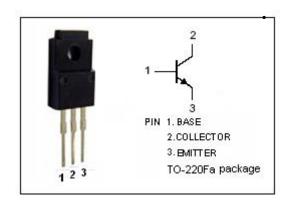
# **isc Silicon NPN Power Transistor**

#### **DESCRIPTION**

- · Collector-Base Breakdown Voltage-
- : V<sub>(BR)CBO</sub>= 800V(Min.)
- Wide Area of Safe Operation
- · High Speed Switching
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

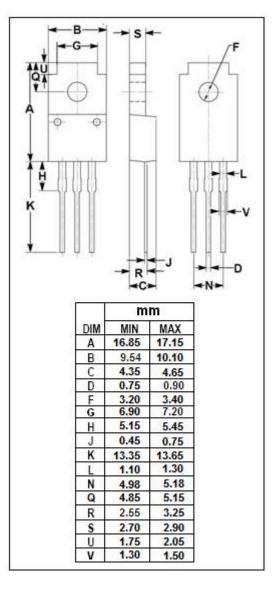
### **APPLICATIONS**

· Designed for high speed switching applications.



## ABSOLUTE MAXIMUM RATINGS (Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	800	V
V <sub>CES</sub>	Collector-Emitter Voltage	800	V
V <sub>CEO</sub>	Collector-Emitter Voltage	500	V
V <sub>EBO</sub>	Emitter-Base Voltage	8	V
Ic	Collector Current-Continuous	7	Α
Ісм	Collector Current-Peak	15	Α
l <sub>Β</sub>	Base Current-Continuous	4	А
Pc	Collector Power Dissipation @T <sub>a</sub> =25°C	2	
	Collector Power Dissipation @T <sub>C</sub> =25°C	45	W
T <sub>j</sub>	Junction Temperature	150	$^{\circ}$
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$





### isc Silicon NPN Power Transistor

2SC3973

#### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT		
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA; I <sub>B</sub> = 0	500			V		
$V_{\text{CE}(\text{sat})}$	Collector-Emitter Saturation Voltage	Ic= 4A; I <sub>B</sub> = 0.8A			1.0	V		
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> = 0.8A			1.5	V		
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 800V; I <sub>E</sub> = 0			100	μА		
ІЕВО	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			100	μА		
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 5V	15					
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 4A; V <sub>CE</sub> = 5V	8					
f⊤	Current-Gain—Bandwidth Product	Ic= 0.5A; VcE= 10V; f= 1MHz		20		MHz		
Switching Times								
t <sub>on</sub>	Turn-on Time				1.0	μS		
ts	Storage Time	I <sub>C</sub> = 4A; I <sub>B1</sub> = 0.8A; I <sub>B2</sub> = -1.6A; V <sub>CC</sub> = 200V			3.0	μS		
t <sub>f</sub>	Fall Time				0.3	μs		

## **NOTICE:**

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